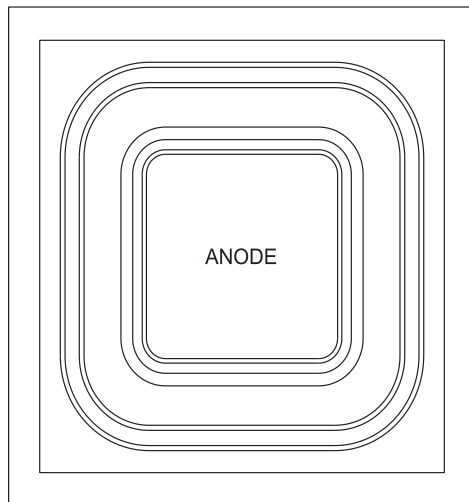


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au.As - 13,000Å

**GEOMETRY**



BACKSIDE CATHODE

**GROSS DIE PER 4 INCH WAFER**

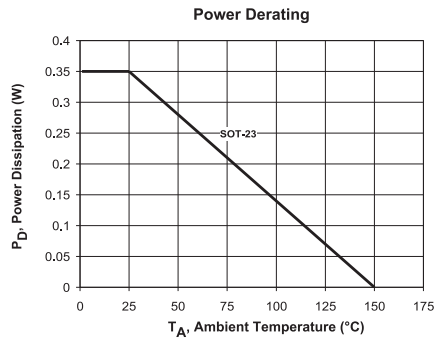
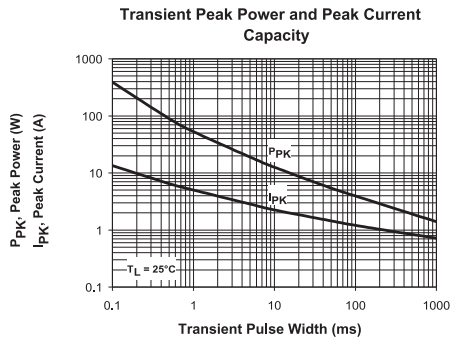
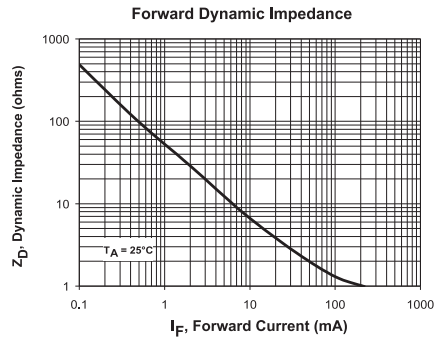
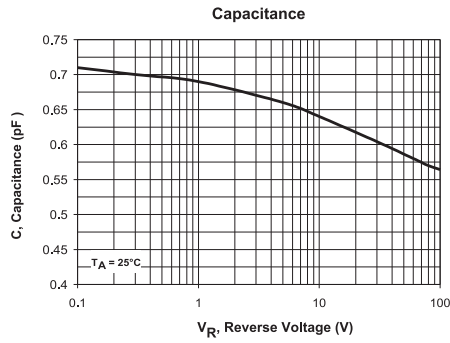
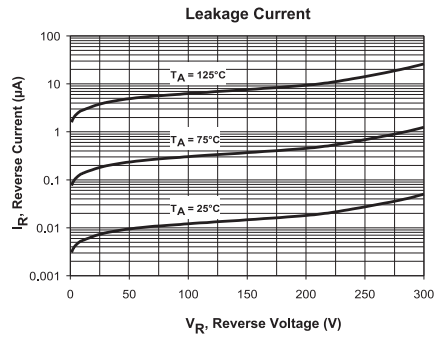
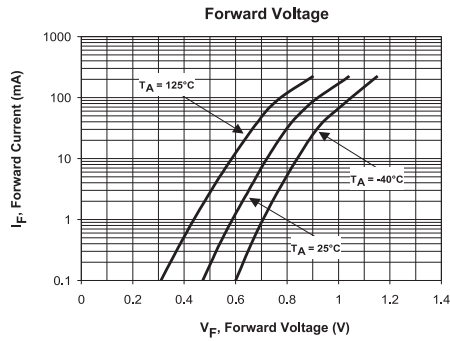
45,050

**PRINCIPAL DEVICE TYPES**

CMPD2003  
CMPD2004  
CMPD2005  
1N3070  
CMDD2004  
CMSD2004  
CMOD2004  
CMXD2004  
CMLD2004

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